2SC3313

Silicon NPN epitaxial planar type

For high-frequency amplification

Features

- Optimum for high-density mounting
- Allowing supply with the radial taping
- Optimum for RF amplification of FM/AM radios

| | Unit: mm |
|-------------|---------------|
| 0.75 max. | 2 |
| (2.5) (2.5) | 0.45+0.20 |
| | 0.7±0.1 |
| | 1: Emitter |
| | 2: Collector |
| | 3: Base |
| | NS-B1 Package |
| | |

Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Parameter | Symbol | Rating | Unit | | |
|---------------------------------------|------------------|-------------|------|--|--|
| Collector-base voltage (Emitter open) | V _{CBO} | 30 | V | | |
| Collector-emitter voltage (Base open) | V _{CEO} | 20 | V | | |
| Emitter-base voltage (Collector open) | V _{EBO} | 5 | V | | |
| Collector current | I _C | 30 | mA | | |
| Collector power dissipation | P _C | 300 | mW | | |
| Junction temperature | Tj | 150 | °C | | |
| Storage temperature | T _{stg} | -55 to +150 | °C | | |
| | | | | | |

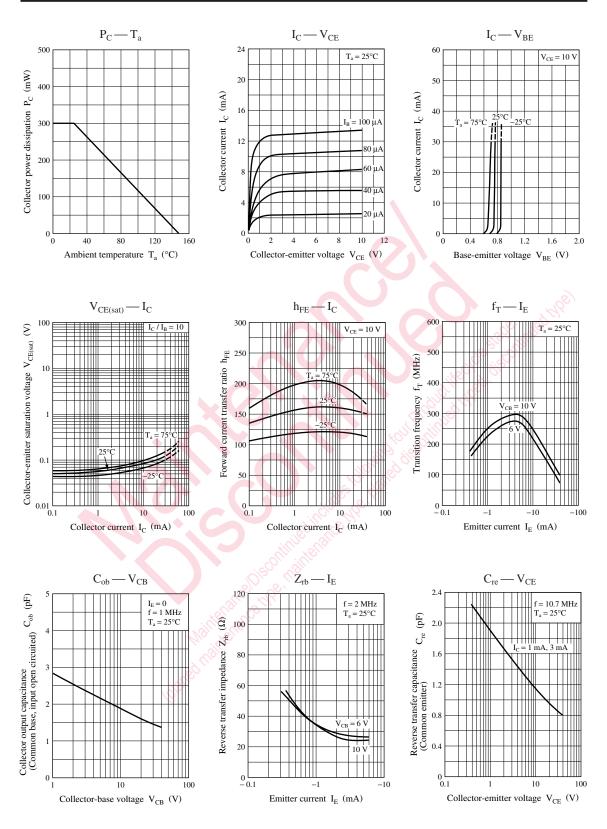
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|------------------|---|-----|-----|-----|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$ | 30 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$ | 20 | | | V |
| Emitter-base voltage (Collector open) | V _{EBO} | $I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$ | 5 | | | V |
| Forward current transfer ratio * | h _{FE} | $V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}$ | 70 | | 250 | — |
| Transition frequency | fT | $V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 200 \text{ MHz}$ | 150 | | | MHz |
| Reverse transfer capacitance (Common emitter) | Cre | $V_{CB} = 10 \text{ V}, \text{ I}_{\text{E}} = -1 \text{ mA}, \text{ f} = 10.7 \text{ MHz}$ | | | 1.6 | pF |
| Reverse transfer impedance | Z _{rb} | $V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 2 \text{ MHz}$ | | | 60 | Ω |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification

| Rank | В | С | | | |
|--------------|-----------|------------|--|--|--|
| $h_{\rm FE}$ | 70 to 160 | 110 to 250 | | | |

Panasonic



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